

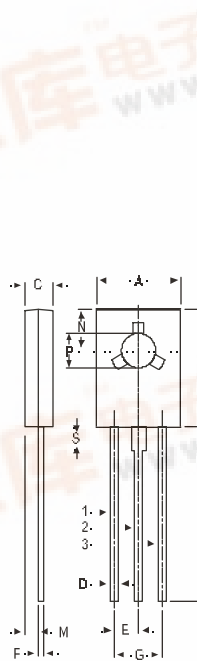
TO-126 (SOT-32) Plastic Package

CSC1162

CSC1162 NPN PLASTIC POWER TRANSISTOR

Complementary CSA715

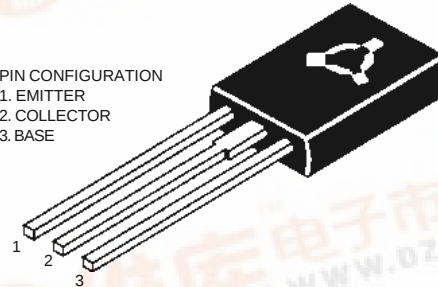
Low frequency Power Amplifier



DIM	MIN.	MAX.
A	7.4	7.8
B	10.5	10.8
C	2.4	2.7
D	0.7	0.9
E	2.25 TYP.	
F	0.49	0.75
G	4.5 TYP.	
L	15.7 TYP.	
M	1.27 TYP.	
N	3.75 TYP.	
P	3.0	3.2
S	2.5 TYP.	

ALL DIMENSIONS IN MM

PIN CONFIGURATION
1. EMITTER
2. COLLECTOR
3. BASE



ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)

Collector-emitter voltage (open base)

Collector current

Total power dissipation up to $T_C = 25^\circ\text{C}$

Junction temperature

Collector-emitter saturation voltage

$I_C = 2\text{A}$; $I_B = 0.2\text{A}$

D.C. current gain

$I_C = 0.5\text{A}$; $V_{CE} = 2\text{V}$

V_{CBO} max. 35 V

V_{CEO} max. 35 V

I_C max. 2.5 A

P_{tot} max. 10 W

T_j max. 150 $^\circ\text{C}$

V_{CEsat} max. 1.0 V

h_{FE} min. 60

max. 320

RATINGS (at $T_A = 25^\circ\text{C}$ unless otherwise specified)

Limiting values

Collector-base voltage (open emitter)

Collector-emitter voltage (open base)

V_{CBO} max. 35 V

V_{CEO} max. 35 V

CSC1162

Emitter-base voltage (open collector)	V_{EBO}	max.	5.0 V
Collector current	I_C	max.	2.5 A
Collector current (Peak)	I_C	max.	3.0 A
Total power dissipation up to $T_A = 25^\circ\text{C}$	P_{tot}	max.	0.75 W
Total power dissipation up to $T_C = 25^\circ\text{C}$	P_{tot}	max.	10 W
Junction temperature	T_j	max.	150 $^\circ\text{C}$
Storage temperature	T_{stg}		65 to +150 $^\circ\text{C}$

CHARACTERISTICS

$T_{amb} = 25^\circ\text{C}$ unless otherwise specified

Collector cutoff current $I_E = 0; V_{CB} = 35\text{V}$	I_{CBO}	max.	20 μA
Breakdown voltages $I_C = 10\text{ mA}; I_E = 0$	V_{CEO}	min.	35 V
$I_C = 1\text{ mA}; I_E = 0$	V_{CBO}	min.	35 V
$I_E = 1\text{ mA}; I_C = 0$	V_{EBO}	min.	5 V
Saturation voltage $I_C = 2\text{ A}; I_B = 0.2\text{ A}$	V_{CEsat}^*	max.	1.0 V
Base-emitter on voltage $I_C = 1.5\text{A}; V_{CE} = 2\text{V}$ (Pulse)	$V_{BE(on)}$	max.	1.5 V
D.C. current gain $I_C = 0.5\text{ A}; V_{CE} = 2\text{ V}^{**}$	h_{FE}	min.	60
		max.	320
$I_C = 1.5\text{ A}; V_{CE} = 2\text{ V}$ (Pulse)	h_{FE}	min.	20
Transition frequency $I_C = 0.2\text{ A}; V_{CE} = 2\text{ V}$	f_T	typ.	180 MHz

**** h_{FE} classification: B: 60-120 C: 100-200 D: 160-320**

[查询"CSC1162C"供应商](#)

Disclaimer

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